Icemos Technology Ltd **Product Specification** **1003.270701** Issue Date 09 March 2015 14:18

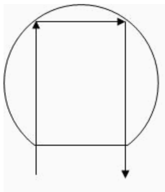
Part Number Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	WaferVendor
	2.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	4.0	Growth Method	CZ	Wafer Vendor
	5.0	Type	N	Wafer Vendor
	6.0	Dopant	Phosphorous	Wafer Vendor
	7.0	Resistivity	1~ 10 ohm cm	Wafer Vendor
	8.0	Overall Thickness	350.00 +/- 5.00 um	Wafer Vendor
	9.0	Total Thickness Variation (TTV)	<1.00um	Guaranteed by process
	9.1	Bow	<50.00um	ADE measurement
	9.2	Warp	<50.00um	ADE measurement
	10.0	Orientation	<100> +/-0.5	Wafer Vendor
	11.0	Back Surface Quality	Polished with light handling marks	Bright Light 100%
	12.0	Front Surface Quality	Prime	Wafer Vendor
	13.0	Edge Chips	None	Bright Light 100% (note 2)
HandleSilicon	13.1	Handle Thickness	350.00 +/- 5.00 um	
DeviceSilicon	14.0	Haze	None	Bright Light, 100% (note 2).
	15.0	Scratches	None	Bright Light, 100% (note 2).

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

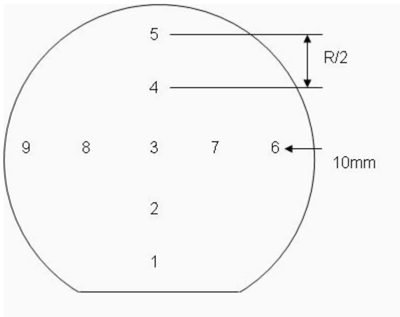
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information